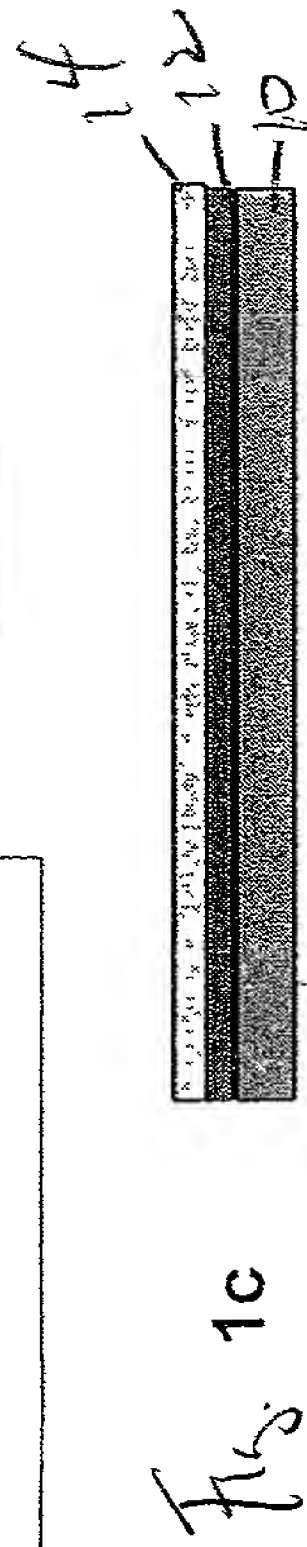
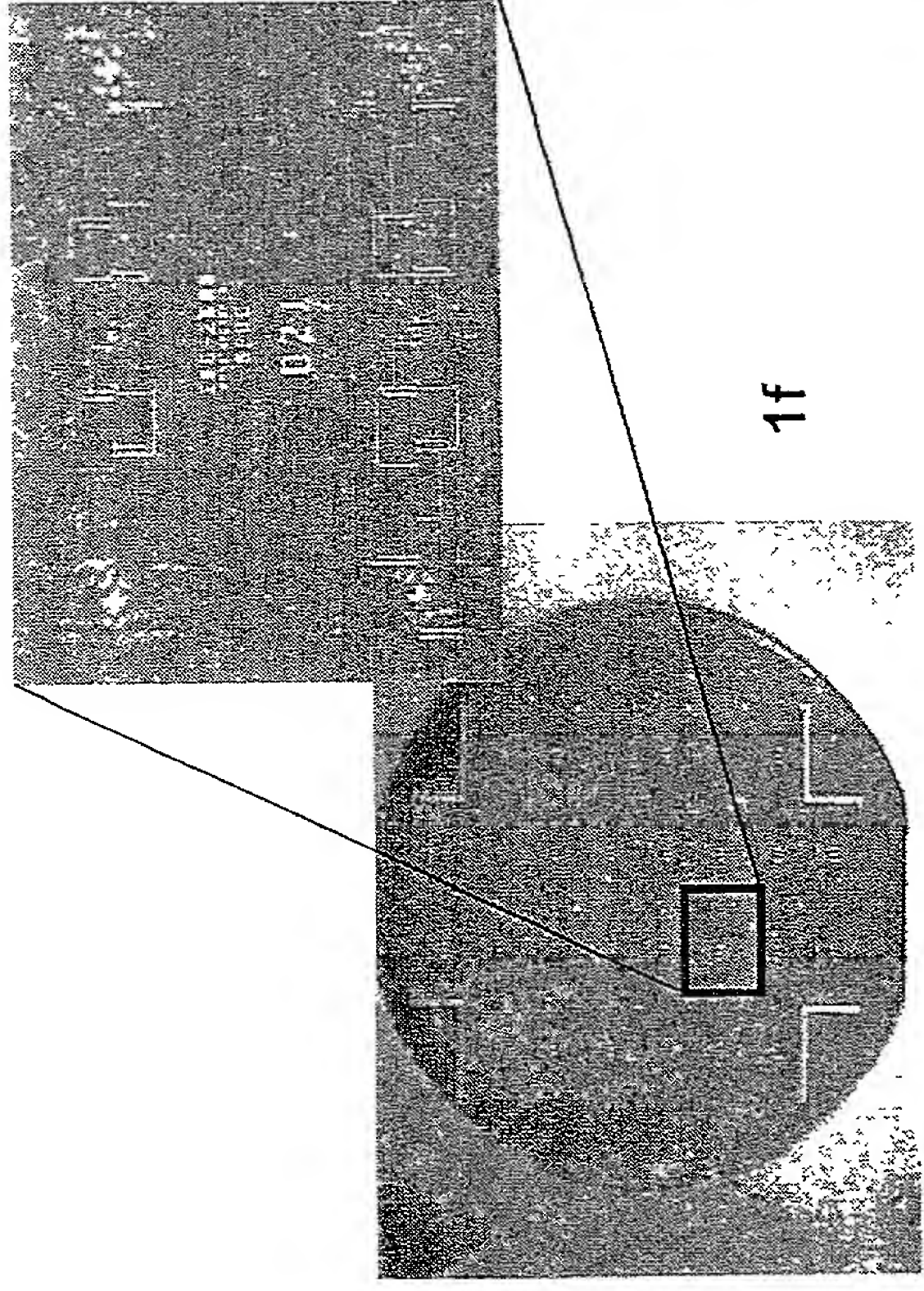
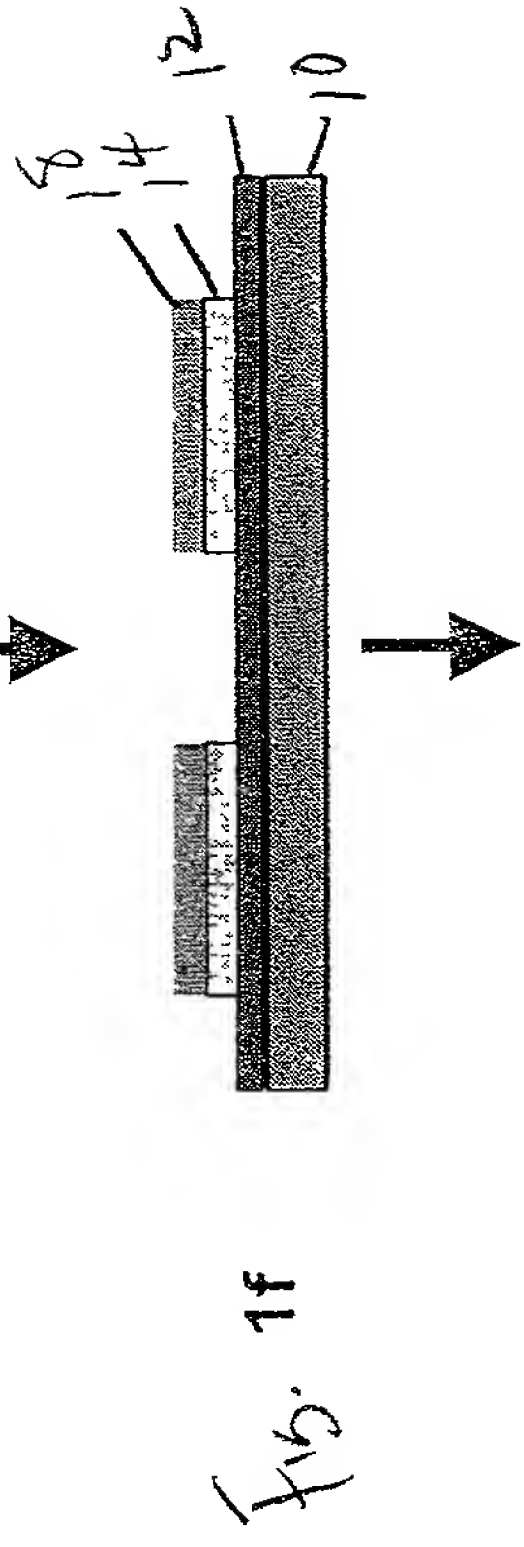
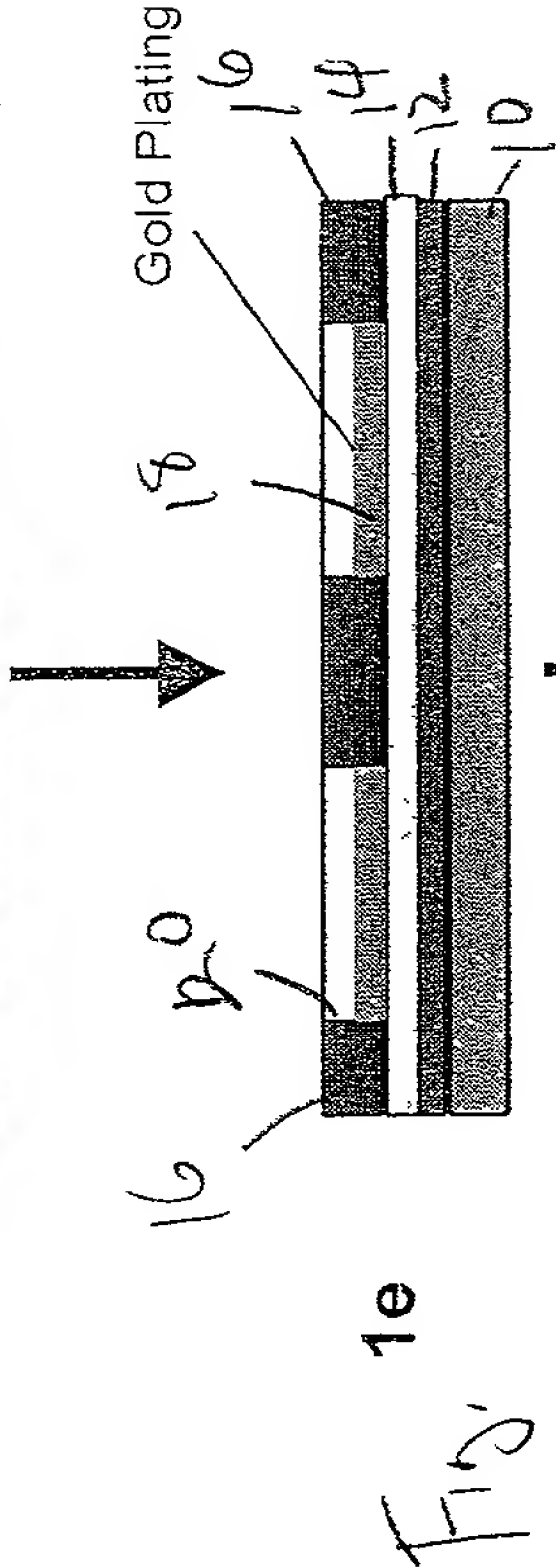
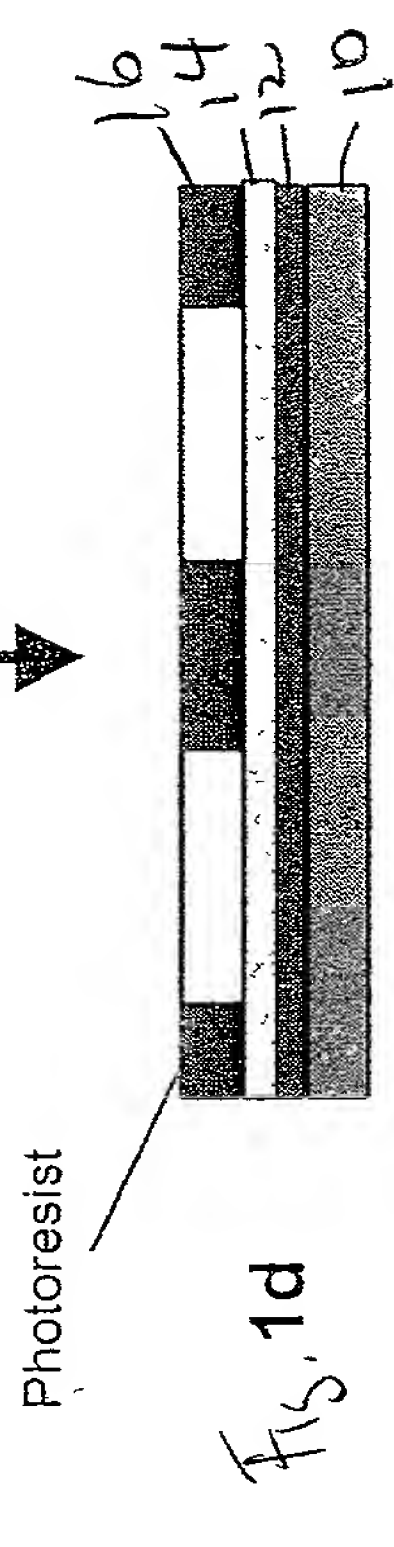


# Reverse Neo Process

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- 1c) Apply field metal
- 1d) Apply photoresist
- 1e) Gold electroplate
- 1f) Strip photoresist & field metal etch



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# Reverse Neo Process

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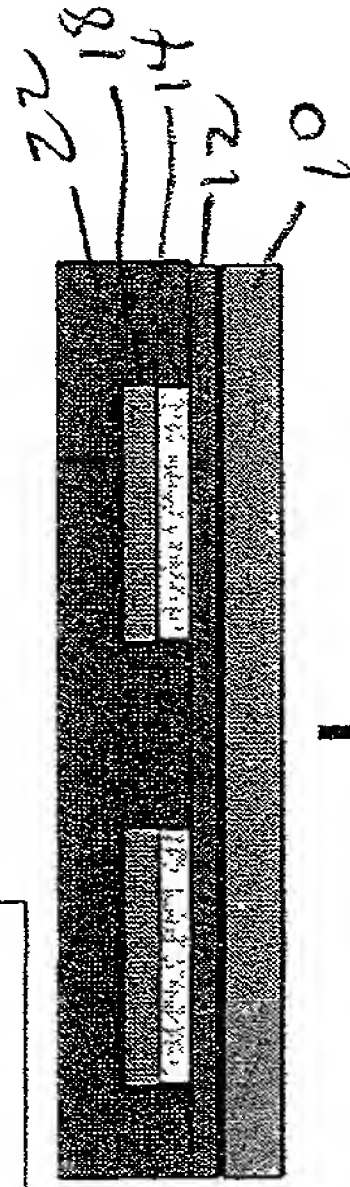


Fig 1g

1g) Apply polyimide

1h) Apply photoresist

1i) Image & develop photoresist & polyimide

1j) Strip photoresist & cure polyimide

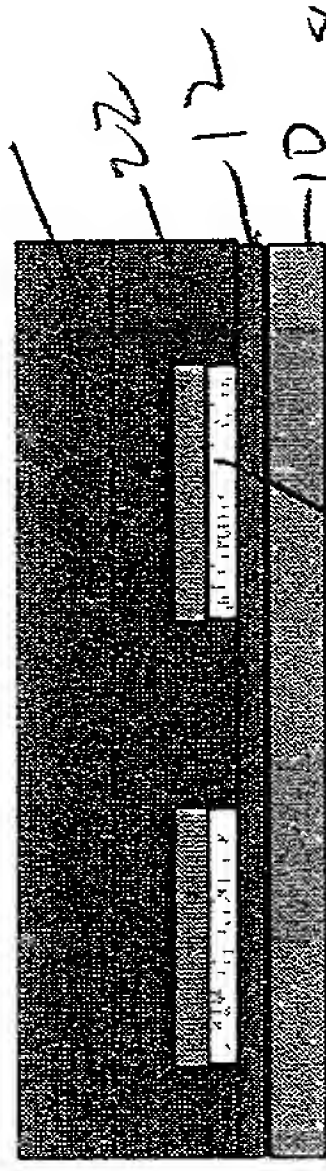


Fig 1h

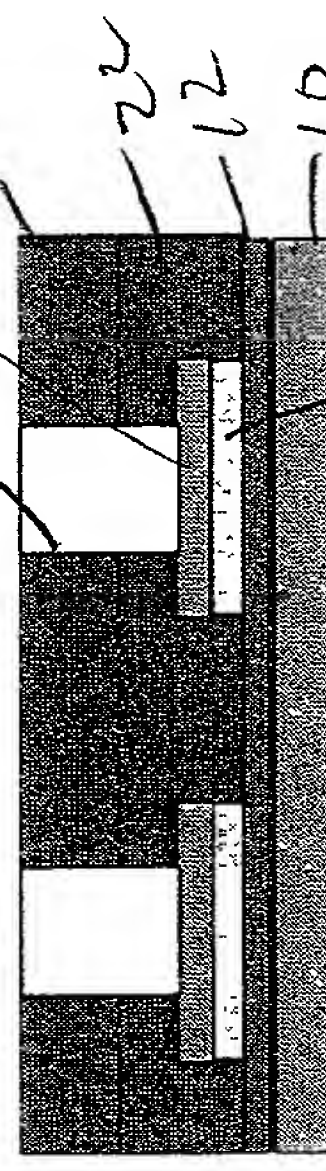


Fig 1i

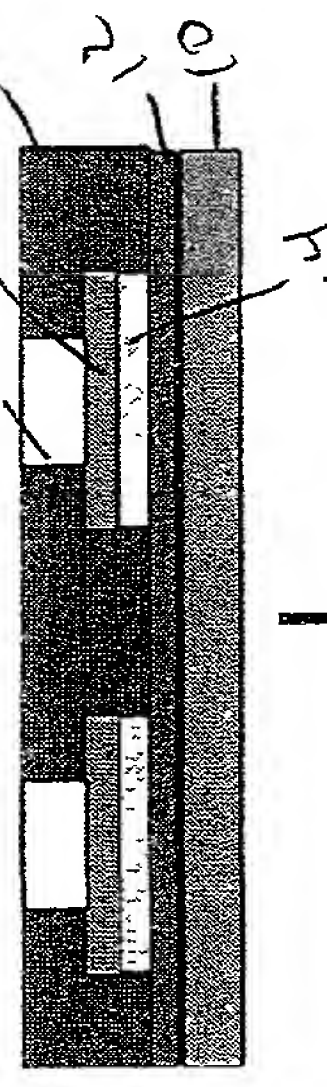


Fig 1j



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# Reverse Neo Process

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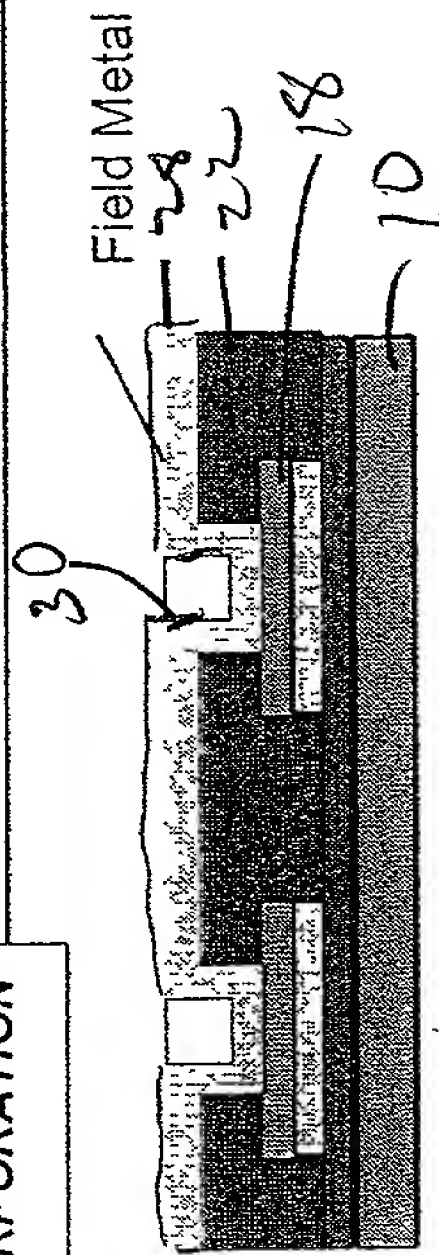


Fig. 1k

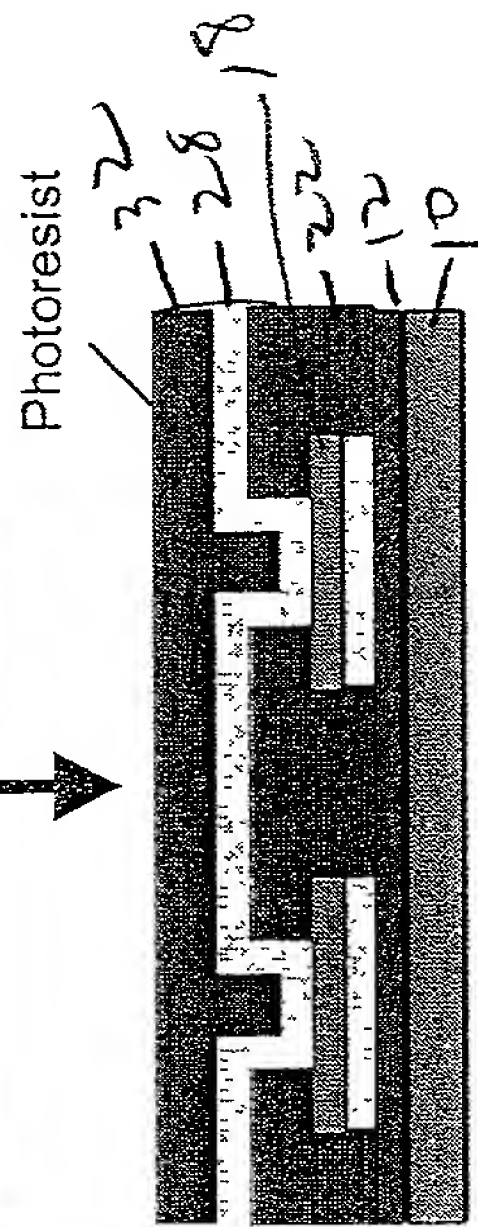


Fig. 1l

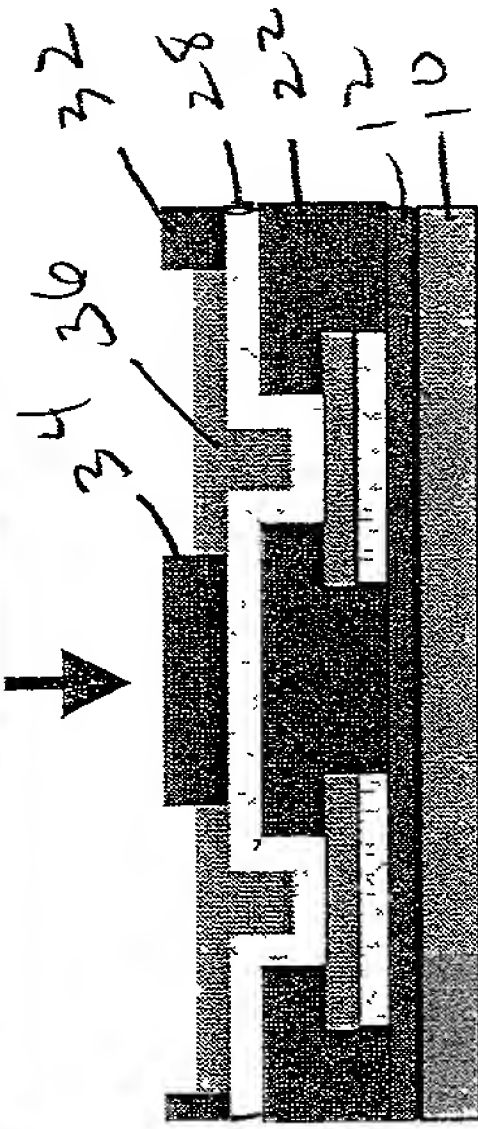


Fig. 1m

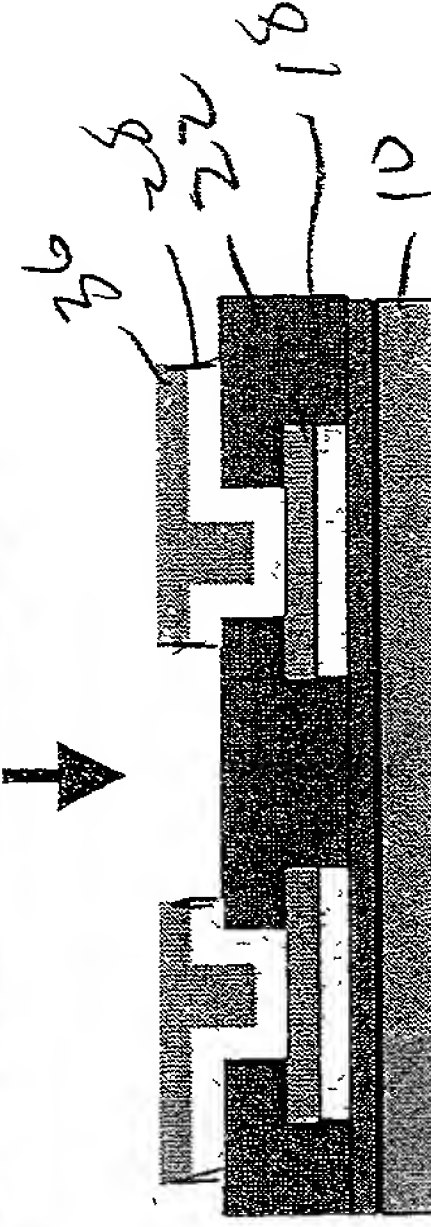


Fig. 1n

- 1k) Apply field metal
- 1l) Apply photoresist
- 1m) Image & develop photoresist. Gold electroplate
- 1n) Strip photoresist & field metal etch

NOTE: For additional layers, steps 1g through 1n are repeated.

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# Reverse Neo Process

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## Solder Bumping Of Die

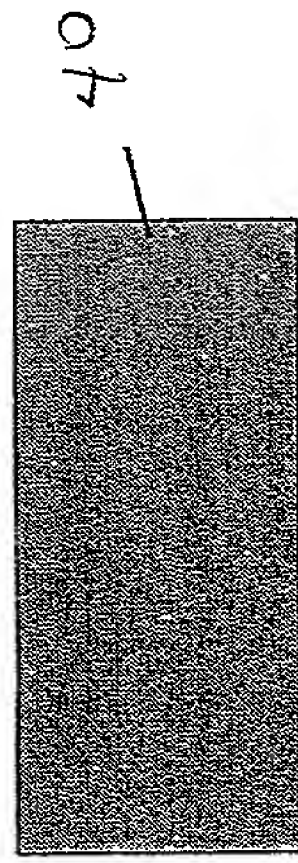


Fig. 2a

- 2a) Retrieve die
- 2b) Apply underbump metalurgy
- 2c) Apply solder bump

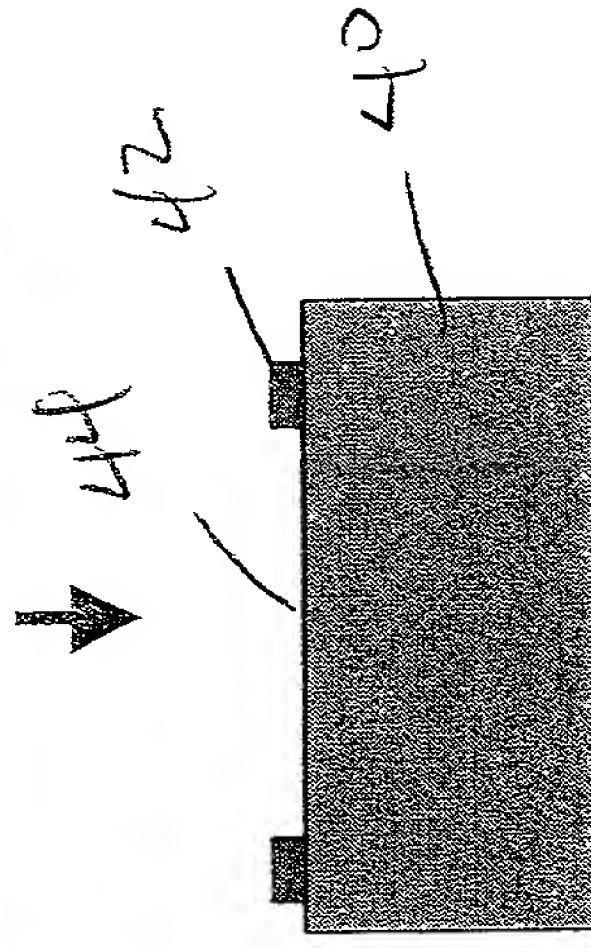


Fig. 2b

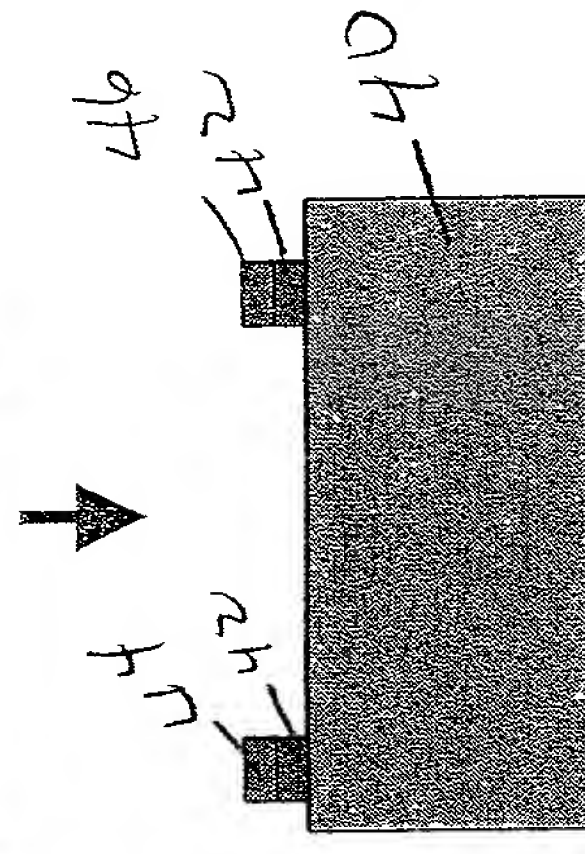
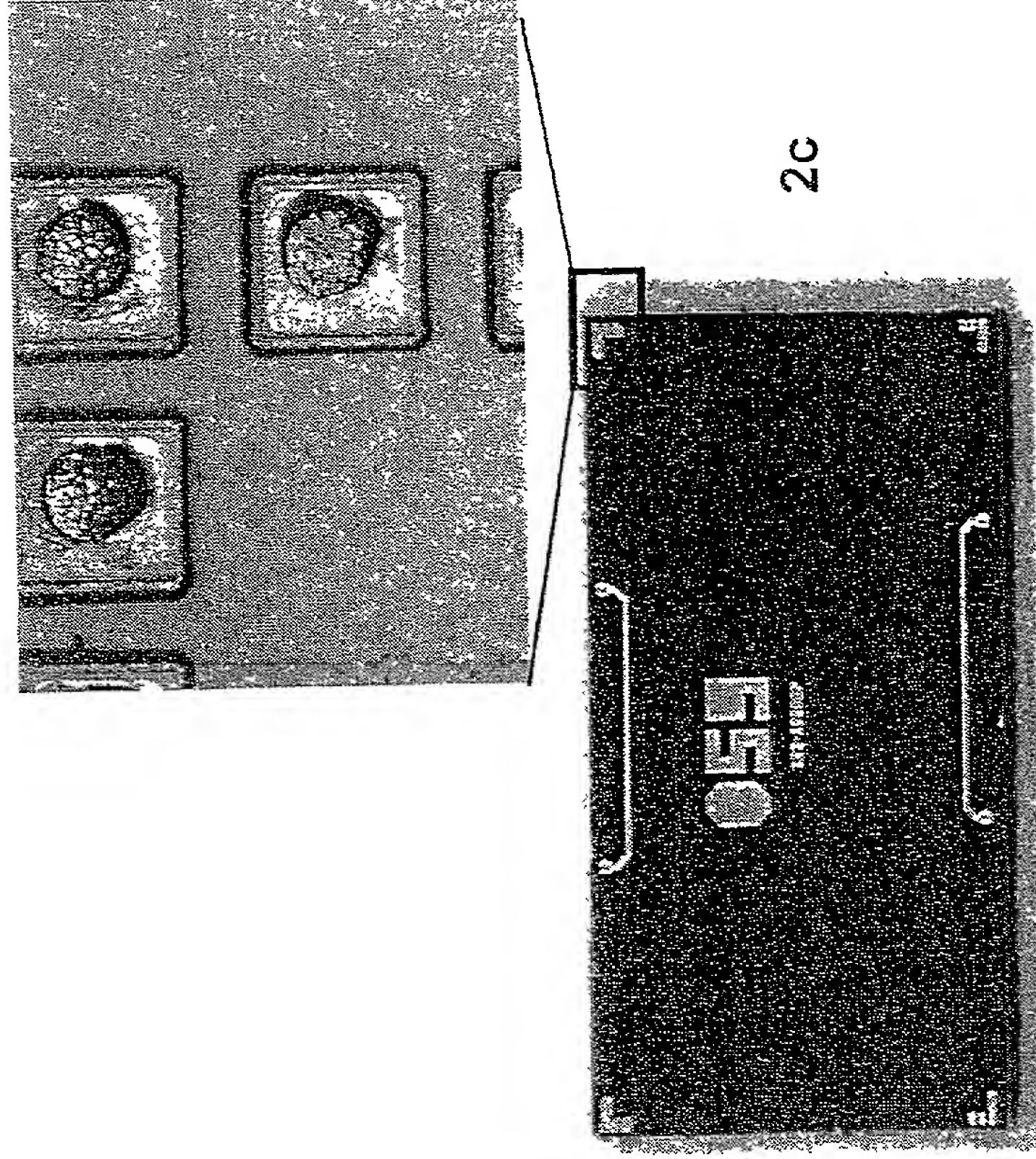


Fig. 2c



2c

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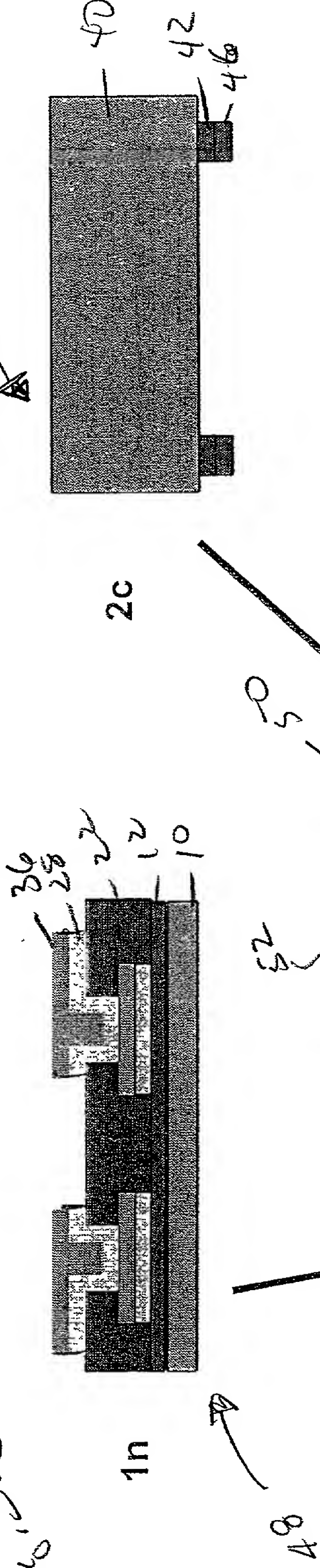
# T011250 33333333 Reverse Neo Process

IRVINE SENSORS CORPORATION

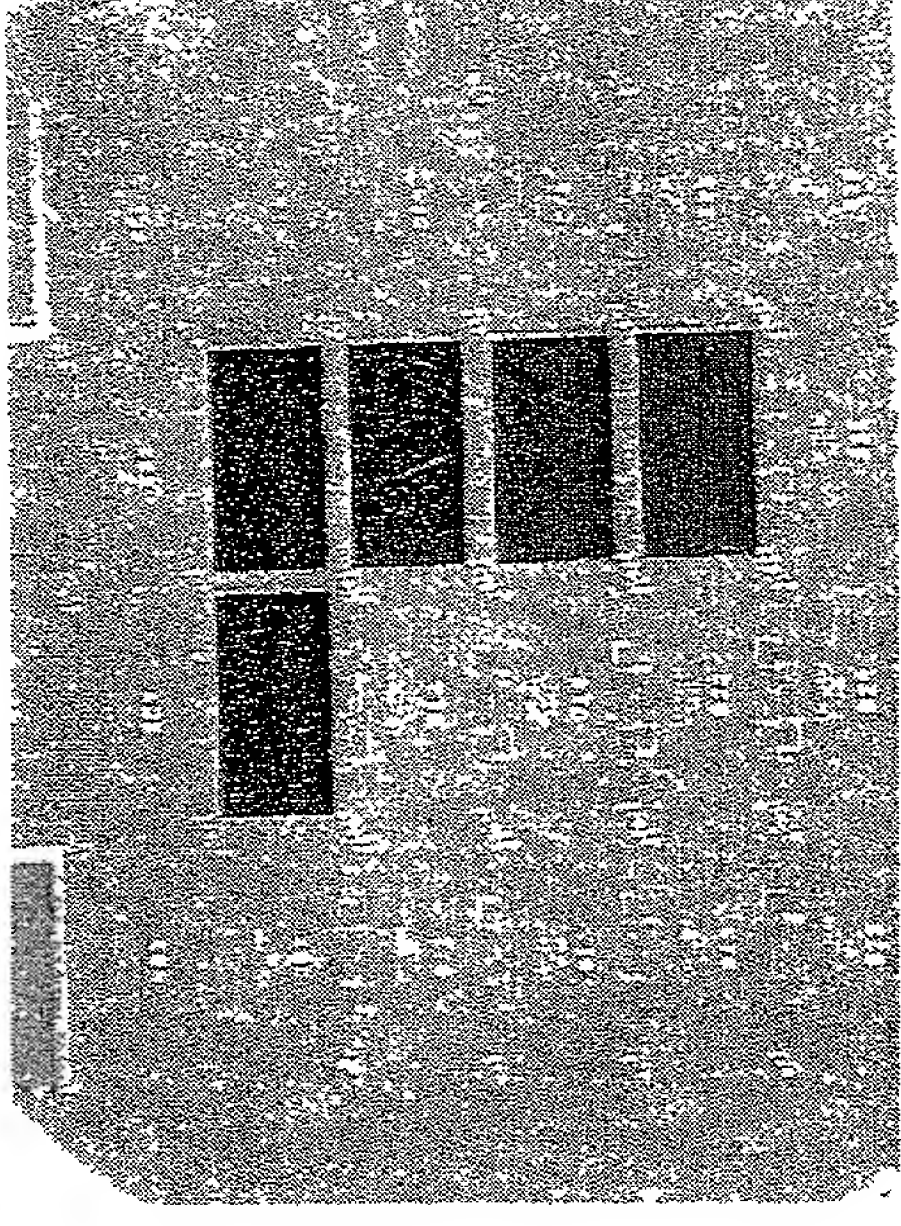
## Flip-Chip Bonding

Fig. 3a

Retrieve substrate assembly and  
bumped die



3a) Flip chip bumped die to substrate

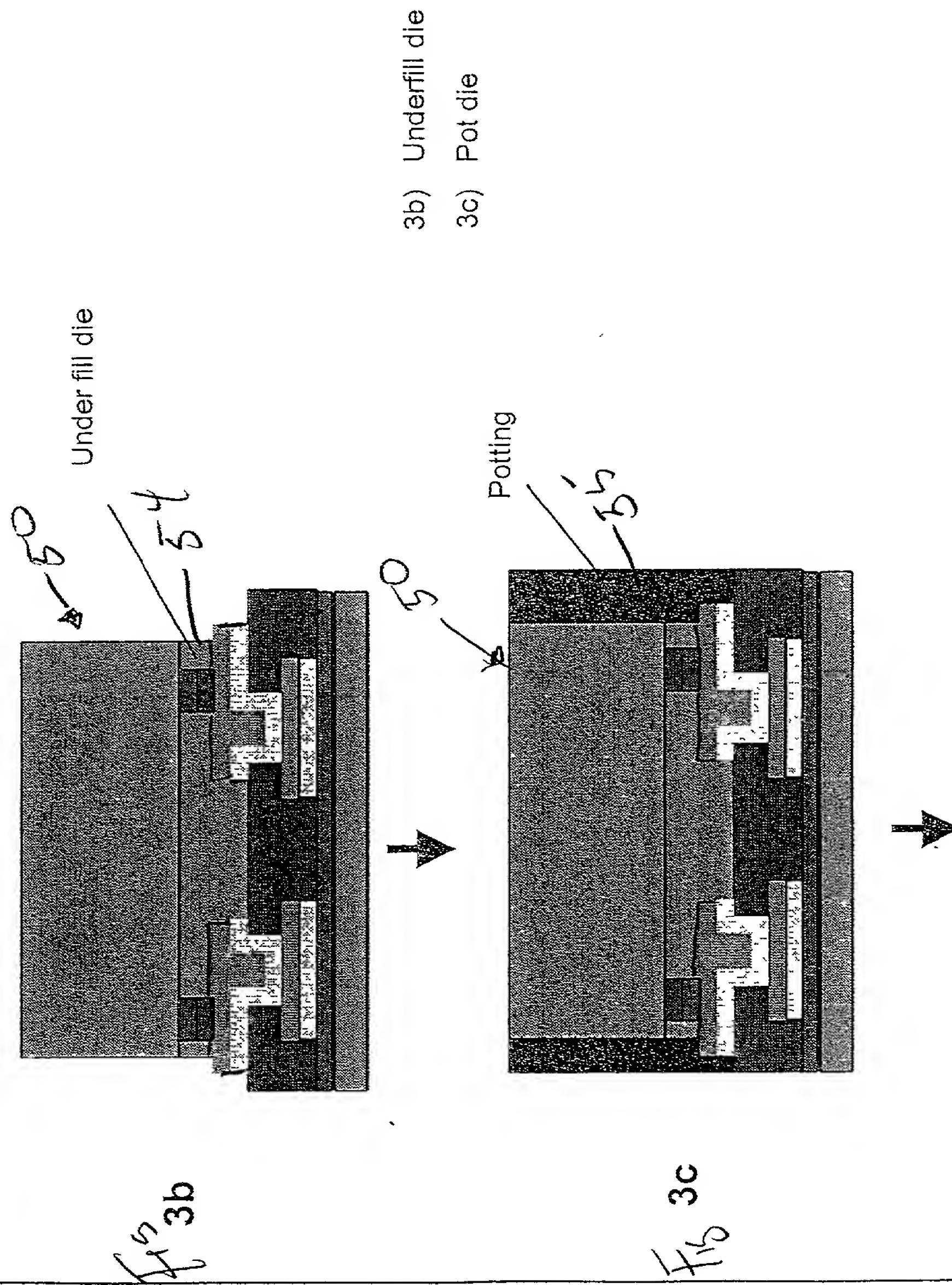


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# Reverse Neo Process

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# Thin Neo Process

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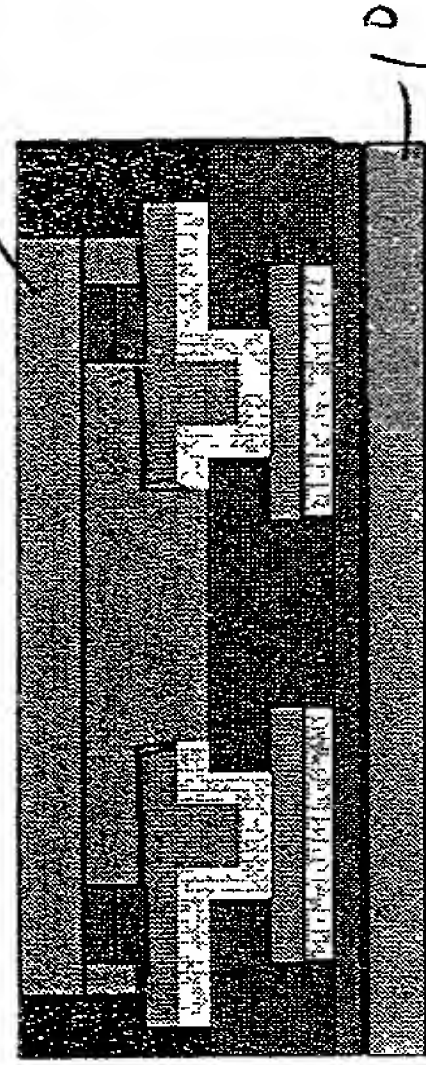


Fig. 3d

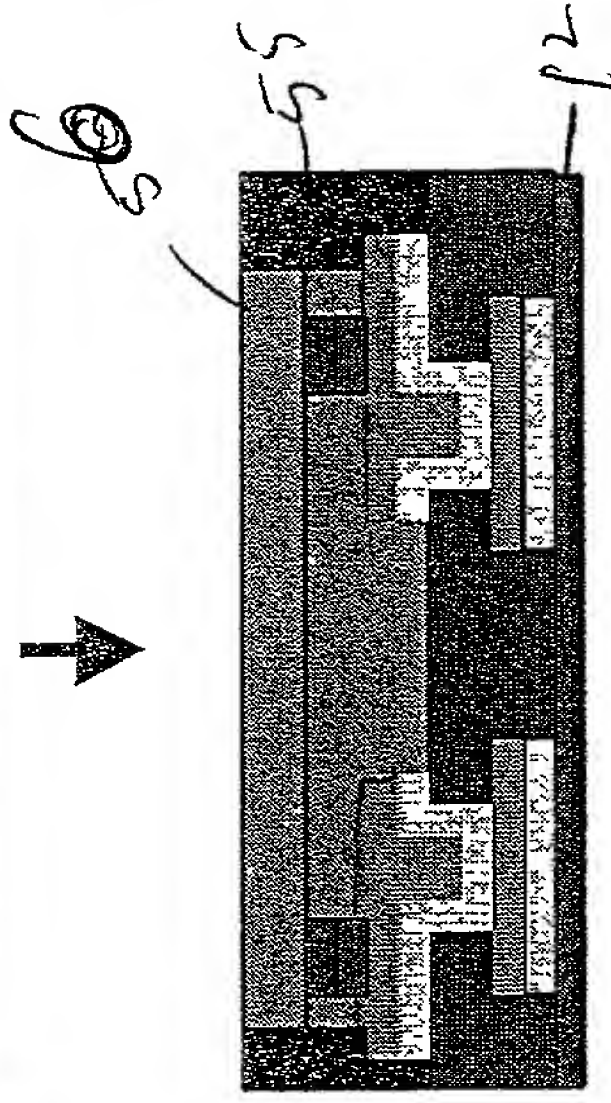


Fig. 3e

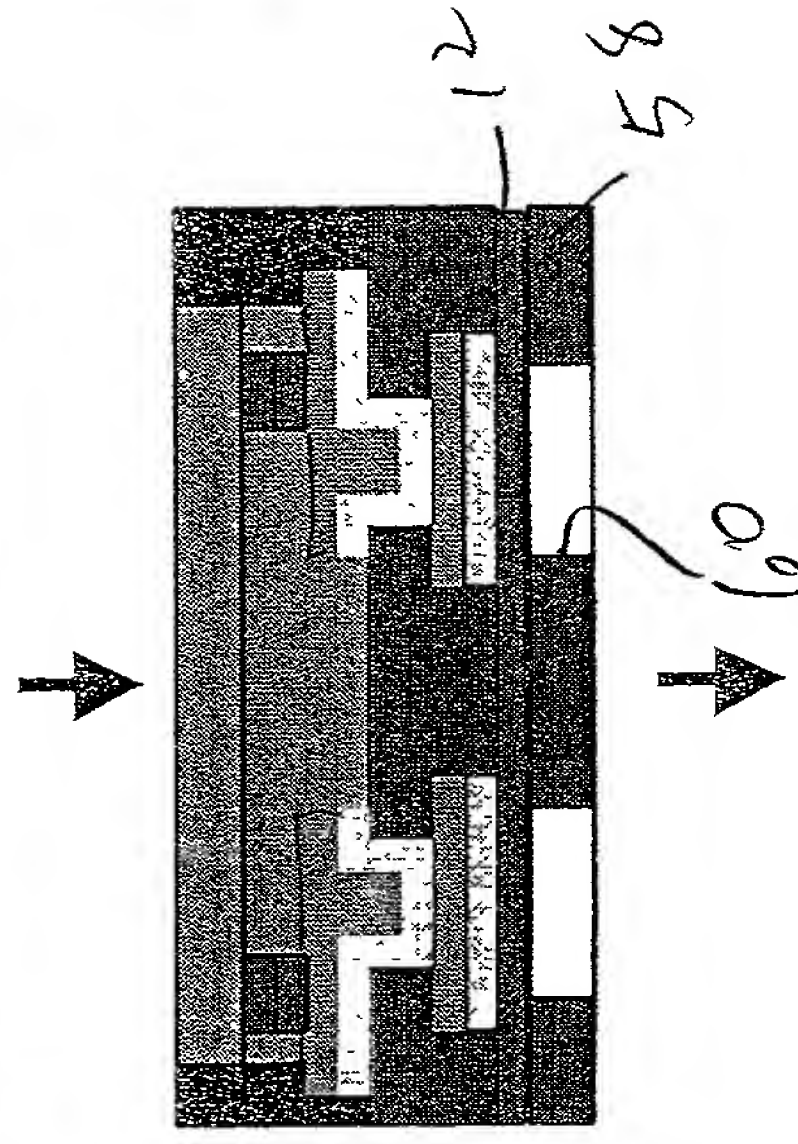
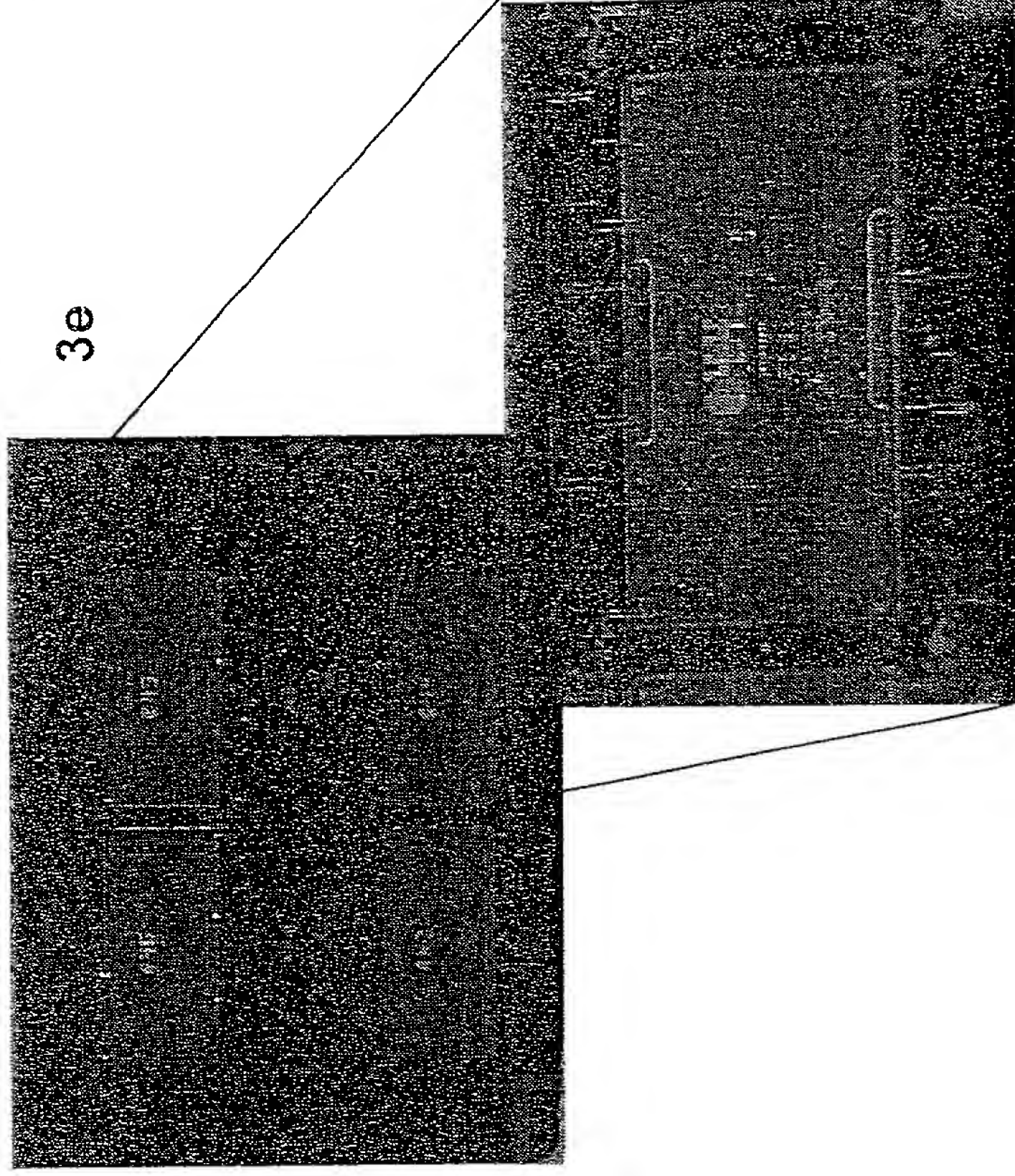


Fig. 3f

- 3d) Thin wafer
- 3e) Release wafer from aluminum substrate
- 3f) Mask wafer for test pad etch



3e

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# Reverse Neo Process

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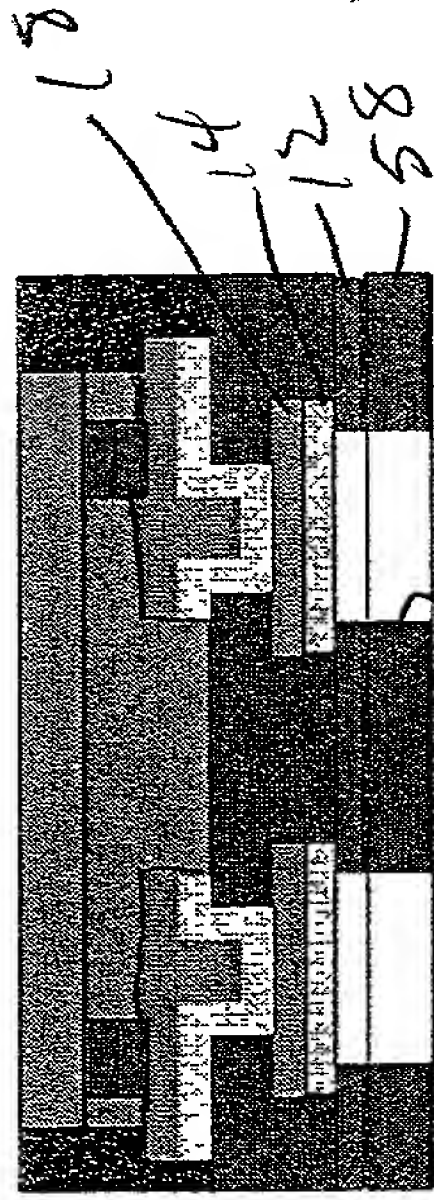


Fig 3g

- 3g) Etch polyimide to expose test pads
- 3h) Remove etch mask & test wafer
- 3i) Dice wafer

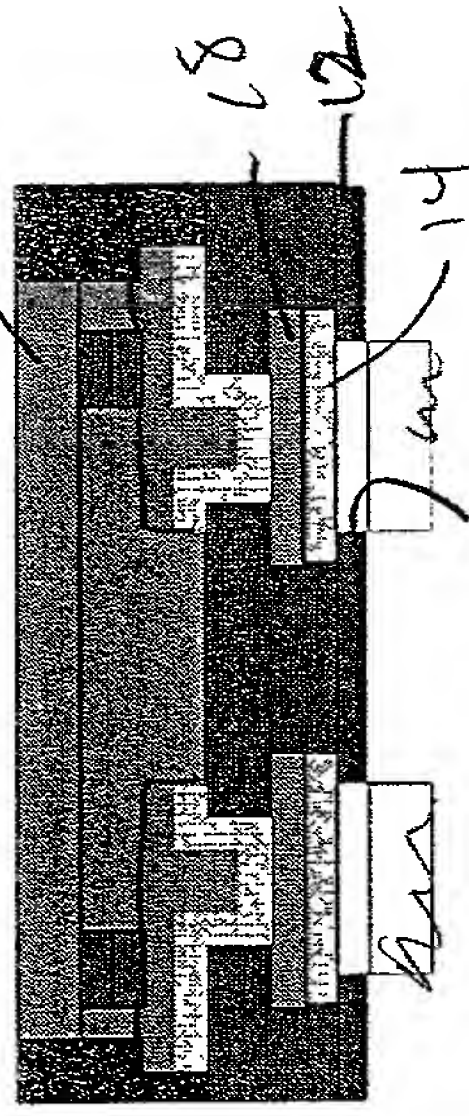


Fig 3h

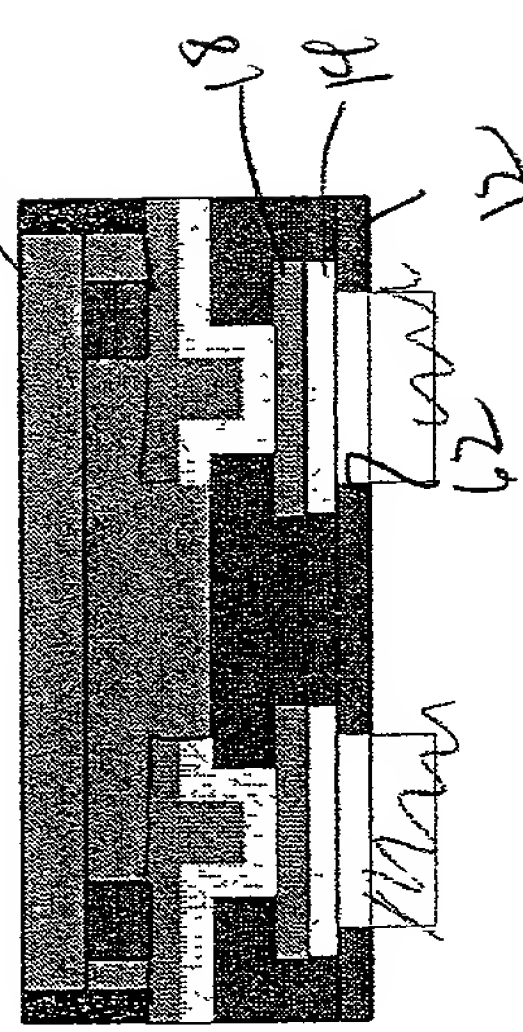
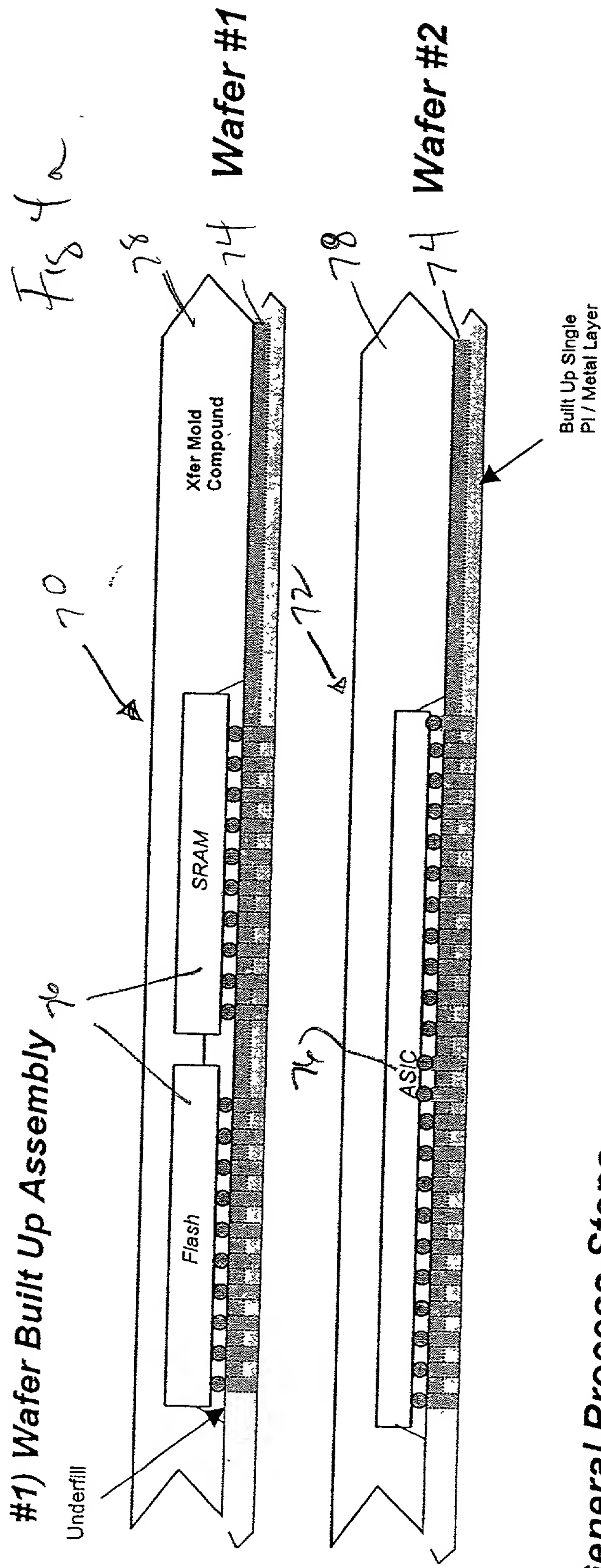


Fig 3i

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# High Volume Reverse NEO Process



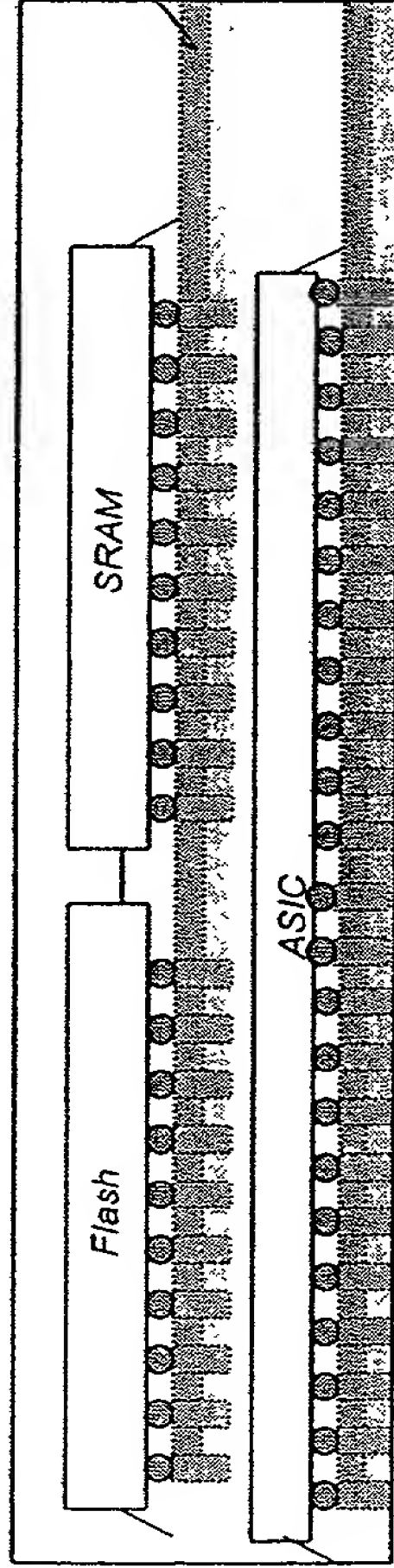
## General Process Steps

- 1) Screen Print Electrically Conductive Epoxy on Built-Up Laminate Substrates
- 2) Place Flip Chip Devices
- 3) Cure Epoxy
- 4) Underfill Devices
- 5) Xfer. Mold Devices

# High Volume Reverse NEO Process

2) Stacked Wafer Strip Assembly

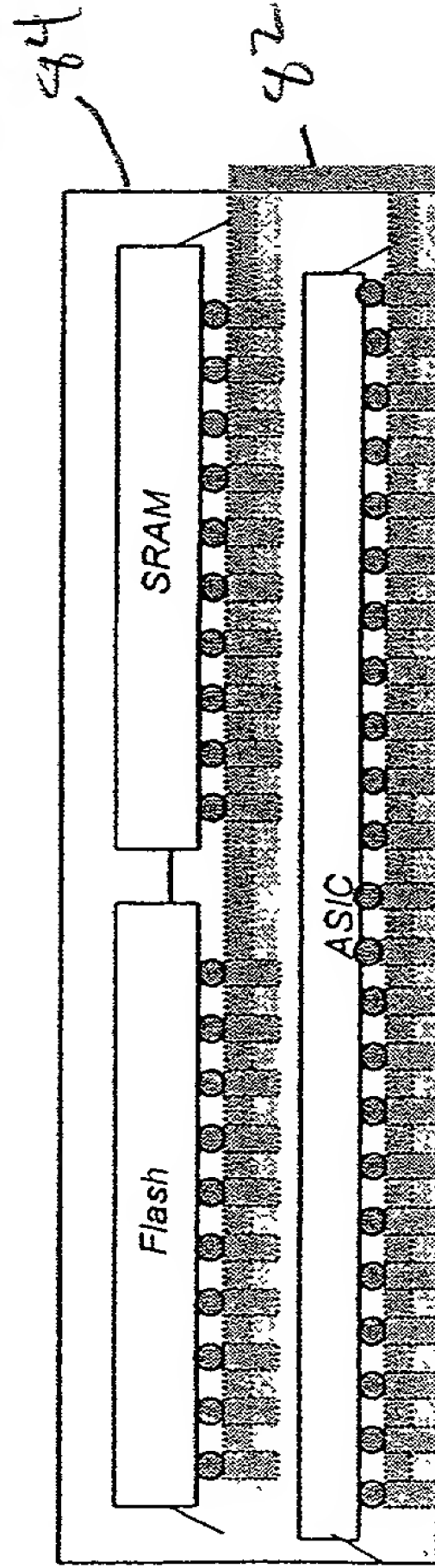
## General Process Steps



- 6) Release Carrier Film from Substrate (If Required)
- 7) Attach Memory and ASIC Wafers
- 8) Cut/Saw Wafers to Strips

3) Stacked Wafer Strip Assembly

## General Process Steps



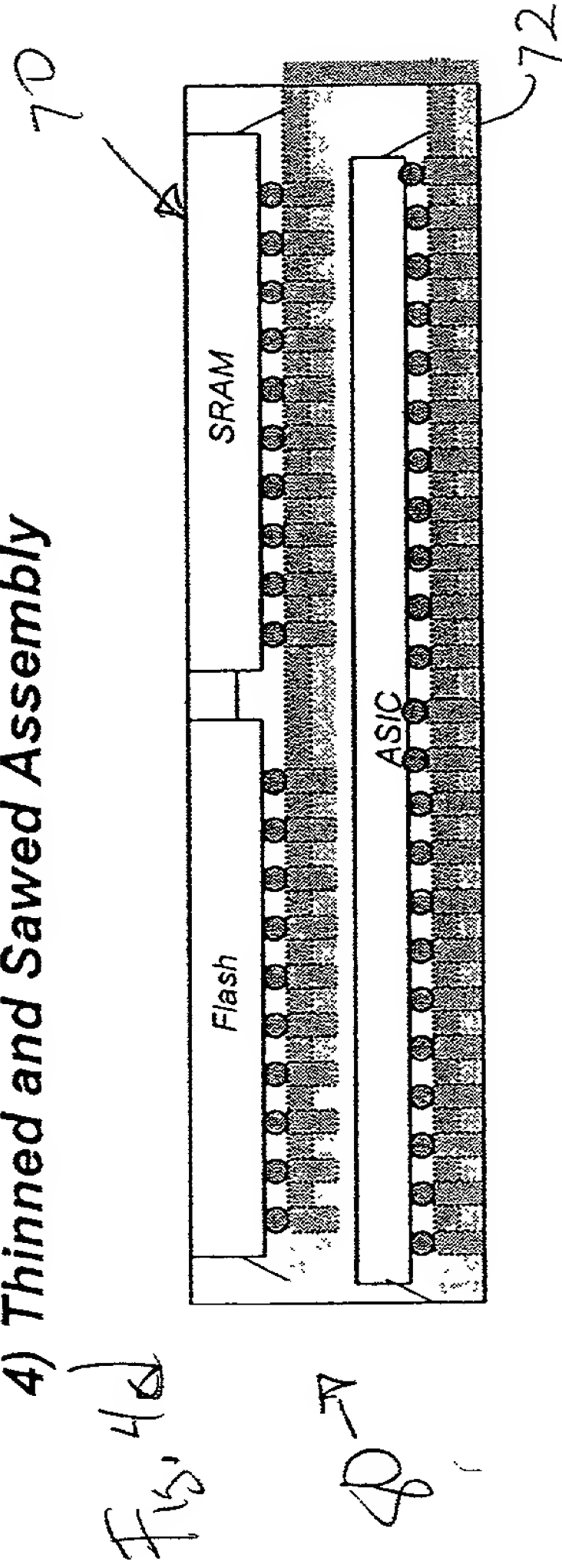
- 9) Interconnect or Bus Wafers by Metallizing Wafer Stacks



# High Volume Reverse NEO Process

## General Process Steps

- 4) Thinned and Sawed Assembly
- 10) Thin Stack Assembly



- 5) Thinned and Sawed Assembly

## General Process Steps

- 11) Solder Bump Stack
- 12) Singulate (Saw) into Individual Stacks

